3DK101

NPN Silicon High Frequency Low Power Switch Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications			Test Condition
			A	B	C	
Total Dissipation	P_{tot}	mW	200			Ta=25°C
Max. Collector Current	I_{CM}	mA	40			
Junction Temperature	T_{jm}	°C	175			
Storage Temperature	T_{stg}	°C	-55~+175			
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	30	30	20	I_C=0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	20	25	15	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4			I_E=0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.3			I_C=20mA I_B=2mA
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	0.9			
C-E Leakage Current	I_{CEO}	uA	0.1			V_{CE}=10V
DC Current Gain	h_{FE}		Orange: 25~40, Yellow: 40~55, Green: 55~80 Blue: 80~120, Purple: 120~180			V_{CE}=1V, I_C=20mA
Transition frequency	f_T	MHz	300			V_{CE}=10V, I_C=10mA f=100MHz
Turn-on Time	ton	ns	30			I_C=10mA I_{B1}= I_{B2}=1mA
Storage Time	ts	ns	40	20	15	
Fall Time	tf	ns	20			

Outline and Dimensions: